优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
100V	8.5mΩ @ V_{GS} = 10V	46A
	13.6mΩ @ V_{GS} = 4.5V	36A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Synchronous rectifiers
- Backlighting
- Power management functions
- DC-DC converters

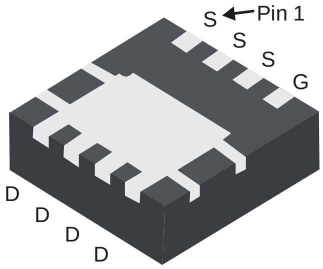
Features and Benefits

- Low $R_{DS(ON)}$ – Ensures On-State Losses are Minimized
- Excellent Q_{gd} x $R_{DS(ON)}$ Product (FOM)
- Advanced Technology for DC/DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application

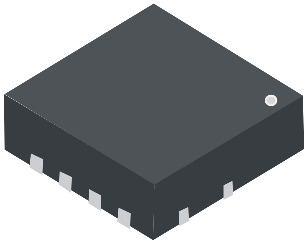
Mechanical Data

- Package: PowerDI®3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.034 grams (Approximate)

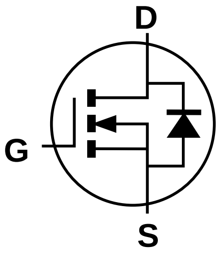
PowerDI3333-8



Bottom View



Top View



Equivalent Circuit

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = 10V	T_A = +25°C T_A = +100°C	I_D	12 8	A
	T_C = +25°C T_C = +100°C	I_D	46 32	A
Maximum Continuous Body Diode Forward Current (Note 5)		I_S	30	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	184	A
Pulsed Body Diode Continuous Current (10µs Pulse, Duty Cycle = 1%)		I_{SM}	184	A
Avalanche Current (L = 1mH)		I_{AS}	17	A
Avalanche Energy (L = 1mH)		E_{AS}	144.5	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	60	°C/W
Total Power Dissipation	T_C = +25°C	P_D	39	W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	3.8	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Note: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 80V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.1	—	2.5	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	6.4	8.5	mΩ	V_{GS} = 10V, I_D = 20A
		—	8.2	13.6		V_{GS} = 4.5V, I_D = 10A
Diode Forward Voltage	V_{SD}	—	0.8	1.2	V	V_{GS} = 0V, I_S = 20A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	2361	—	pF	V_{DS} = 50V, V_{GS} = 0V f = 1MHz
Output Capacitance	C_{oss}	—	611	—		
Reverse Transfer Capacitance	C_{rss}	—	16	—		
Gate Resistance	R_g	—	1.7	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	41	—	nC	V_{DD} = 50V, I_D = 13A V_{GS} = 10V
Gate-Source Charge	Q_{gs}	—	7.3	—		
Gate-Drain Charge	Q_{gd}	—	9.3	—		
Turn-On Delay Time	$t_{D(ON)}$	—	7	—	ns	V_{DD} = 50V, V_{GS} = 10V I_D = 13A, R_g = 6Ω
Turn-On Rise Time	t_R	—	12	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	42	—		
Turn-Off Fall Time	t_F	—	24	—		
Reverse Recovery Time	t_{RR}	—	45	—	ns	I_F = 13A, dI/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	—	68	—	nC	

Notes: 6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

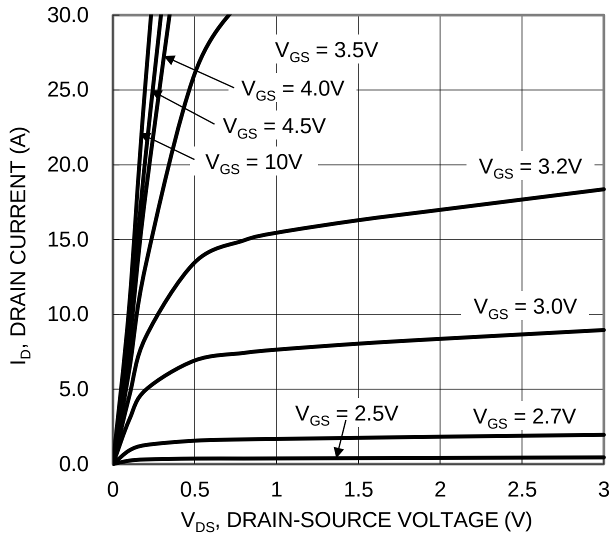


Figure 1. Typical Output Characteristic

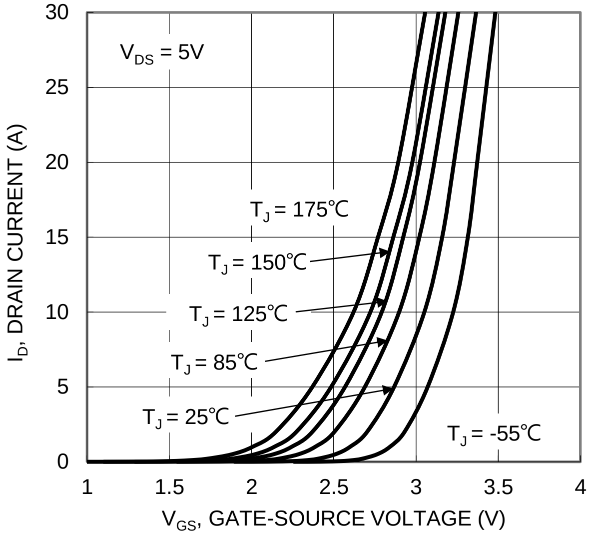


Figure 2. Typical Transfer Characteristic

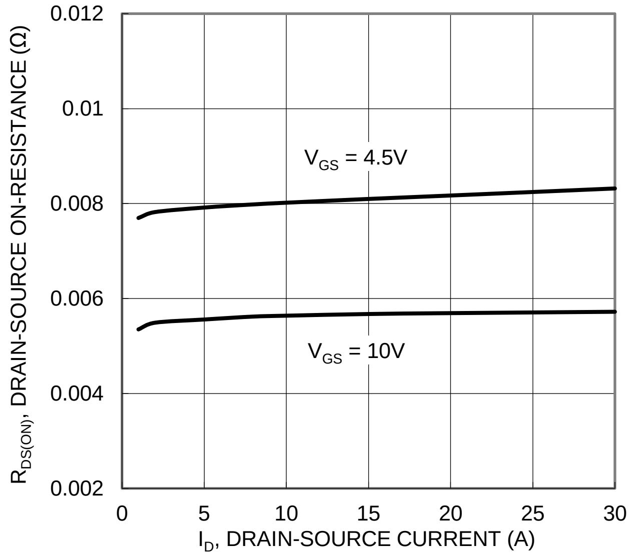


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

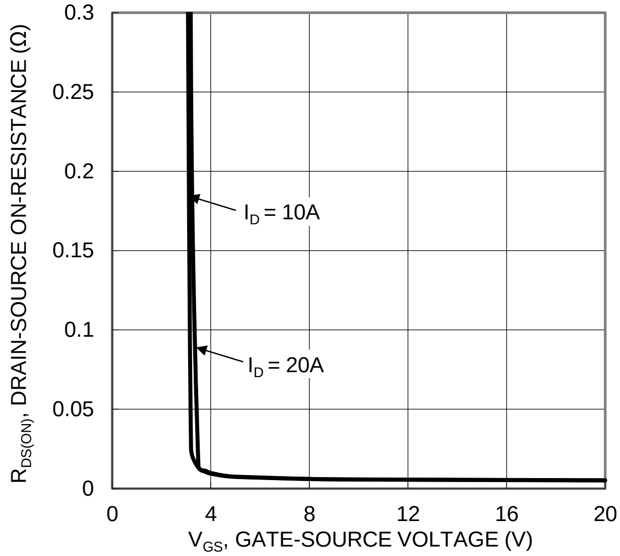


Figure 4. Typical Transfer Characteristic

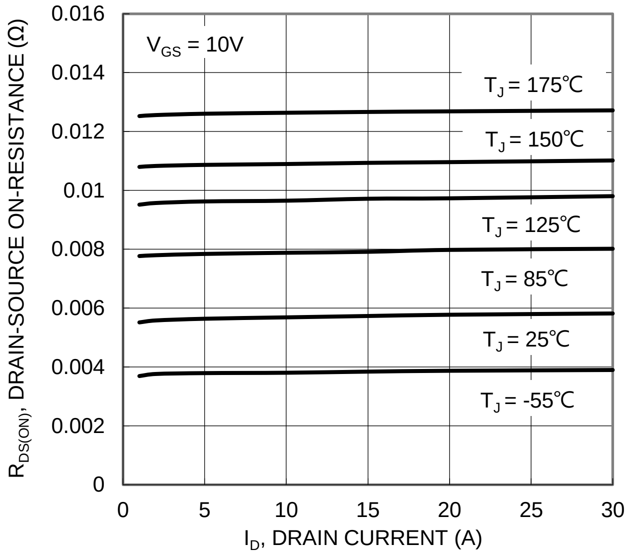


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

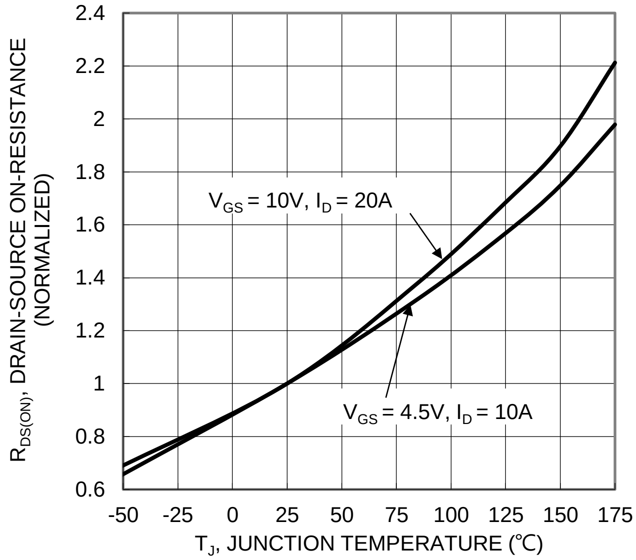


Figure 6. On-Resistance Variation with Junction Temperature

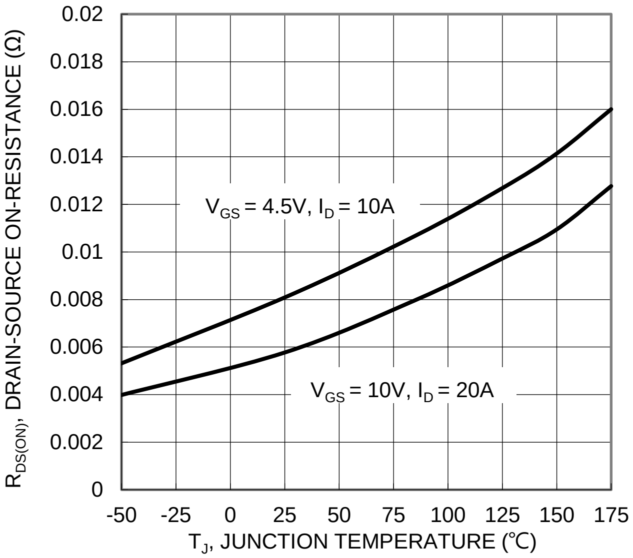


Figure 7. On-Resistance Variation with Junction Temperature

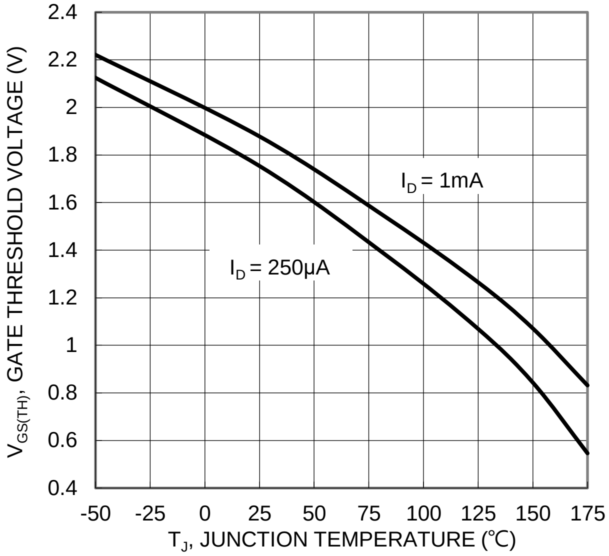


Figure 8. Gate Threshold Variation vs. Junction Temperature

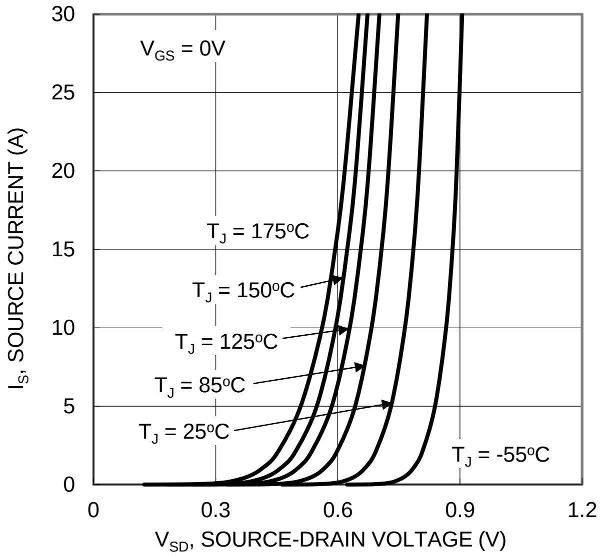


Figure 9. Diode Forward Voltage vs. Current

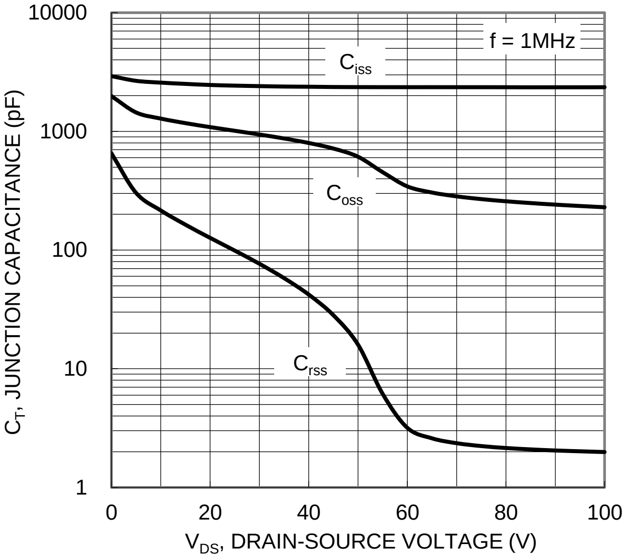


Figure 10. Typical Junction Capacitance

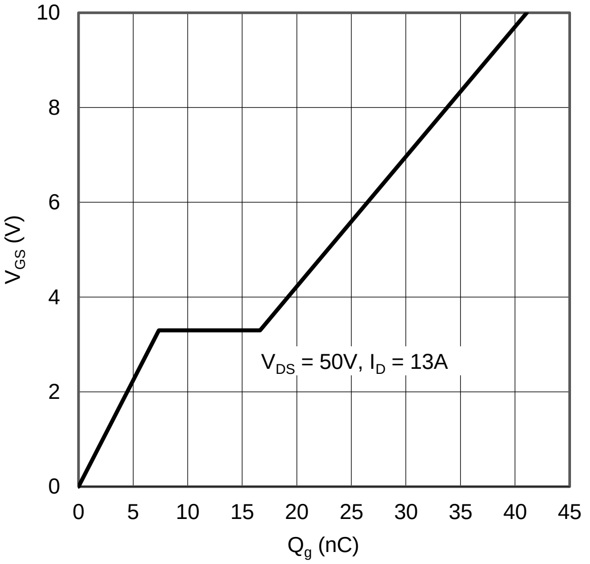


Figure 11. Gate Charge

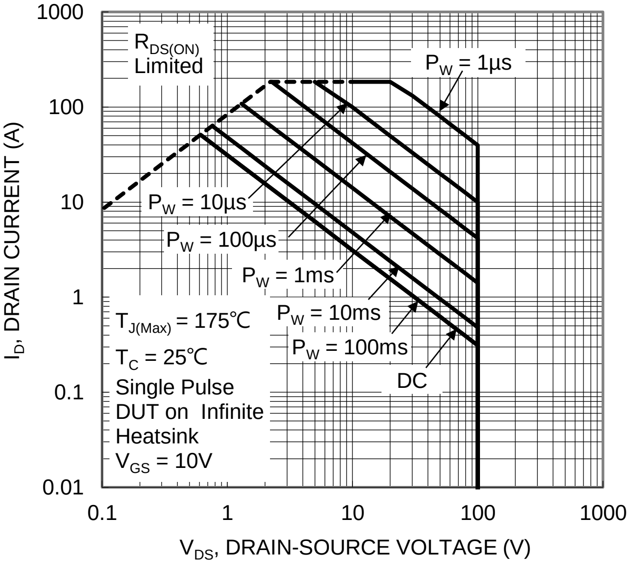


Figure 12. SOA, Safe Operation Area

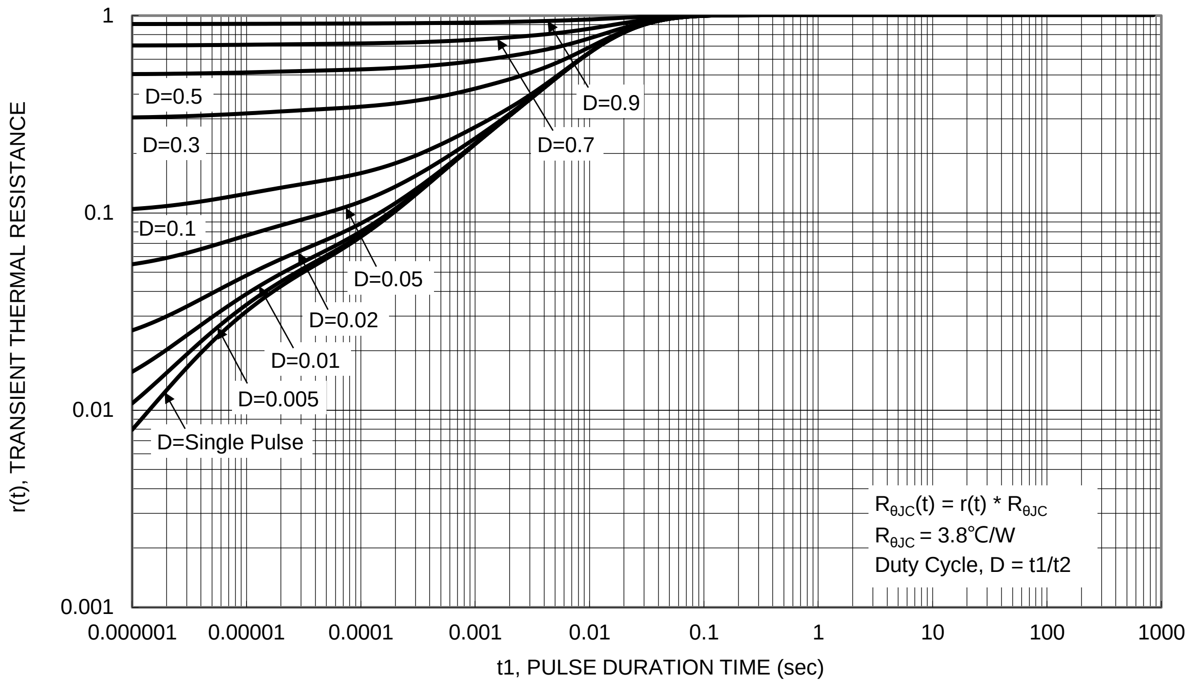
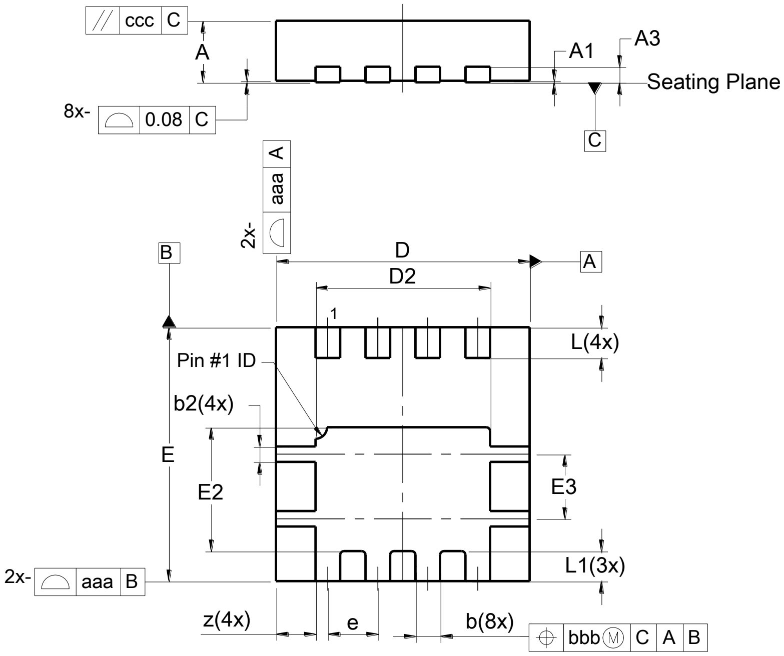


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

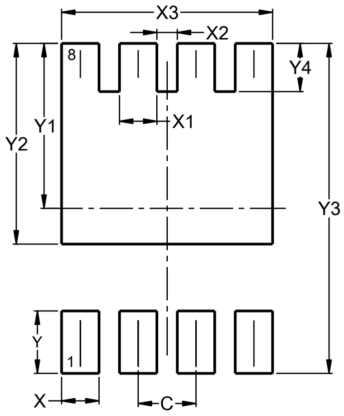
PowerDI3333-8



PowerDI3333-8			
Dim	**Min**	**Max**	**Typ**
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	–	–	0.203
b	0.27	0.37	0.32
b2	–	–	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
e	–	–	0.65
L	0.35	0.45	0.40
L1	–	–	0.39
z	–	–	0.515
aaa	0.25		
bbb	0.10		
ccc	0.10		
All Dimensions in mm			

Suggested Pad Layout

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540